

# PMN48XP

# 20 V, 4.1 A P-channel Trench MOSFET Rev. 1 — 21 April 2011

Product data sheet

#### **Product profile** 1.

## 1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT457 (SC-74) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

## 1.2 Features and benefits

- Low R<sub>DSon</sub>
- Very fast switching

Trench MOSFET technology

# 1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

#### 1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	[1]	-	-	-4.1	Α
Static charact	eristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$		-	48	55	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

#### **Pinning information** 2.

Table 2. **Pinning information** 

	•	,		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	П. П. П.	<b>D</b>
2	D	drain	<u> </u>	
3	G	gate	0	
4	S	source	1 1 2 3	
5	D	drain	SOT457 (TSOP6)	Ś
6	D	drain		017aaa094



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# 3. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMN48XP	TSOP6	plastic surface-mounted package (TSOP6); 6 leads	SOT457		

# 4. Marking

#### Table 4. Marking codes

Type number	Marking code
PMN48XP	ZV

# 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u>	-	-4.1	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-2.5	Α
I <sub>DM</sub>	peak drain current	$T_{amb} = 25 \text{ °C}$ ; single pulse; $t_p \le 10 \mu\text{s}$		-	-20	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	530	mW
			<u>[1]</u>	-	1285	mW
		T <sub>sp</sub> = 25 °C		-	6250	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1.4	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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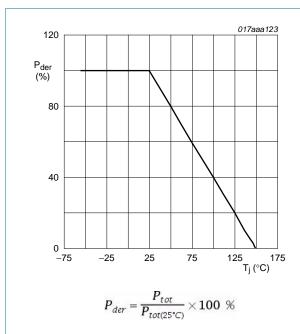


Fig 1. Normalized total power dissipation as a function of junction temperature

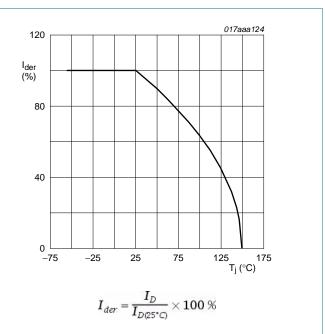
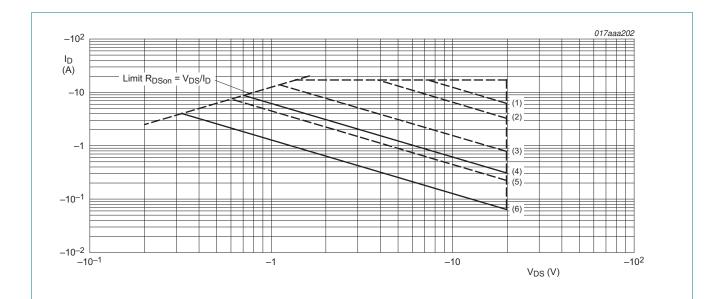


Fig 2. Normalized continuous drain current as a function of junction temperature

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 $I_{DM}$  = single pulse

(1)  $t_p = 100 \ \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3)  $t_p = 10 \text{ ms}$ 

(4) DC;  $T_{sp} = 25 \, ^{\circ}\text{C}$ 

(5)  $t_p = 100 \text{ ms}$ 

(6) DC;  $T_{amb} = 25 \text{ °C}$ ; drain mounting pad 6 cm<sup>2</sup>

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 20 V, 4.1 A P-channel Trench MOSFET

# 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance	in free air	<u>[1]</u>	-	204	235	K/W
	from junction to ambient		[2]	-	84	97	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	17	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

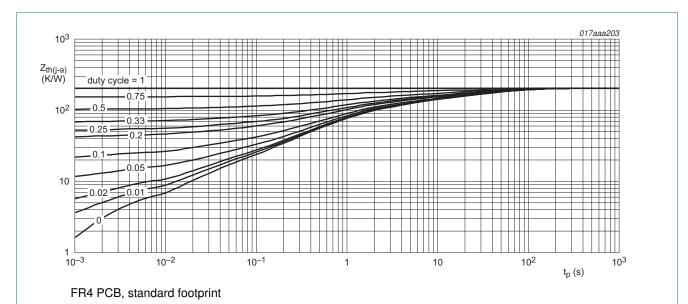
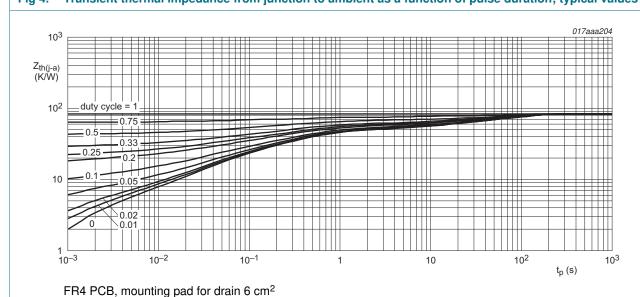


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



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Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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# 7. Characteristics

**Table 7. Characteristics** 

Table 1.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	48	55	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 150 °C	-	70	80	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -2 \text{ A}; T_j = 25 \text{ °C}$	-	72	82	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -2.4 \text{ A}; T_j = 25 \text{ °C}$	-	10	-	S
Dynamic	characteristics					
$Q_{G(tot)}$	total gate charge	$I_D = -1 A$ ; $V_{DS} = -10 V$ ; $V_{GS} = -4.5 V$ ;	-	8.7	13	nC
$Q_GS$	gate-source charge	T <sub>j</sub> = 25 °C	-	1.8	-	nC
$Q_GD$	gate-drain charge		-	1.7	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = -10 \text{ V}; f = 1 \text{ MHz};$	-	1000	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	130	-	рF
C <sub>rss</sub>	reverse transfer capacitance		-	90	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = \text{-10 V};  V_{GS} = \text{-5 V};  R_{G(ext)} = 6  \Omega; $	-	15	-	ns
t <sub>r</sub>	rise time	$T_j = 25 ^{\circ}\text{C}; I_D = -1 ^{\circ}\text{A}$	-	22	-	ns
$t_{d(off)}$	turn-off delay time		-	51	-	ns
t <sub>f</sub>	fall time		-	22	-	ns
Source-d	rain diode					
$V_{SD}$	source-drain voltage	$I_S = -2.4 \text{ A}$ ; $V_{GS} = 0 \text{ V}$ ; $T_i = 25 \text{ °C}$	-	-0.75	-1	V

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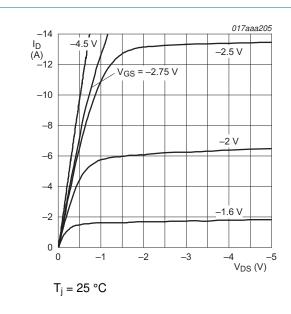
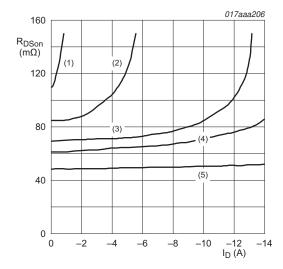


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



(1) 
$$V_{GS} = -1.6 \text{ V}$$

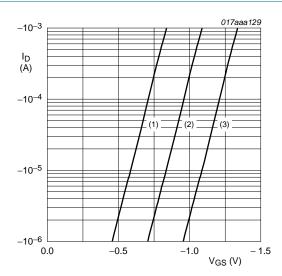
(2) 
$$V_{GS} = -2.0 \text{ V}$$

(3) 
$$V_{GS} = -2.5 \text{ V}$$

(4) 
$$V_{GS} = -2.75 \text{ V}$$

(5) 
$$V_{GS} = -4.5 \text{ V}$$

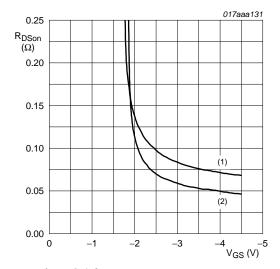
Fig 8. Drain-source on-state resistance as a function of drain current; typical values



$$T_j = 25$$
 °C;  $V_{DS} = -3$  V

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



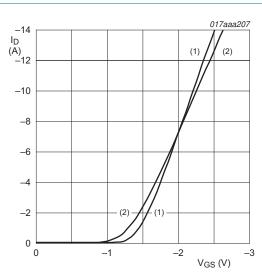
$$I_D = -2.4 A$$

(1) 
$$T_i = 125 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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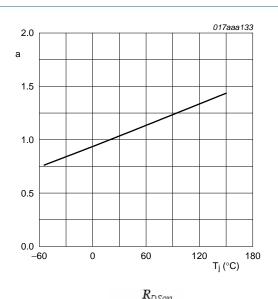


$$V_{DS} > I_{D} \times R_{DSon}$$

(1) 
$$T_i = 25 \, ^{\circ}C$$

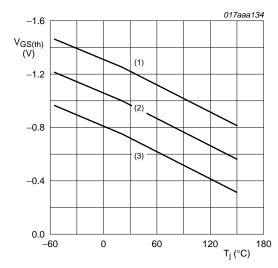
(2) 
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



Normalized drain-source on-state re

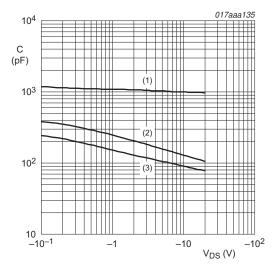
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

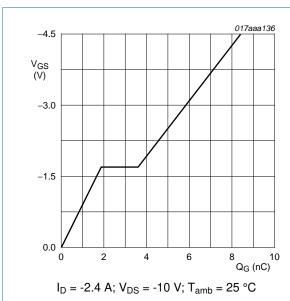


 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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V<sub>GS</sub>(pl)

V<sub>GS</sub>(pl)

V<sub>GS</sub>(th)

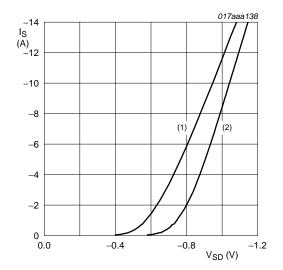
V<sub>GS</sub>

Q<sub>GS1</sub>
Q<sub>GS2</sub>
Q<sub>G</sub>(tot)

017aaa137

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$ 

(1)  $T_j = 150 \, ^{\circ}\text{C}$ 

(2) T<sub>j</sub> = 25 °C

Fig 16. Source current as a function of source-drain voltage; typical values

## 20 V, 4.1 A P-channel Trench MOSFET

# 8. Package outline

## Plastic surface-mounted package (TSOP6); 6 leads

**SOT457** 

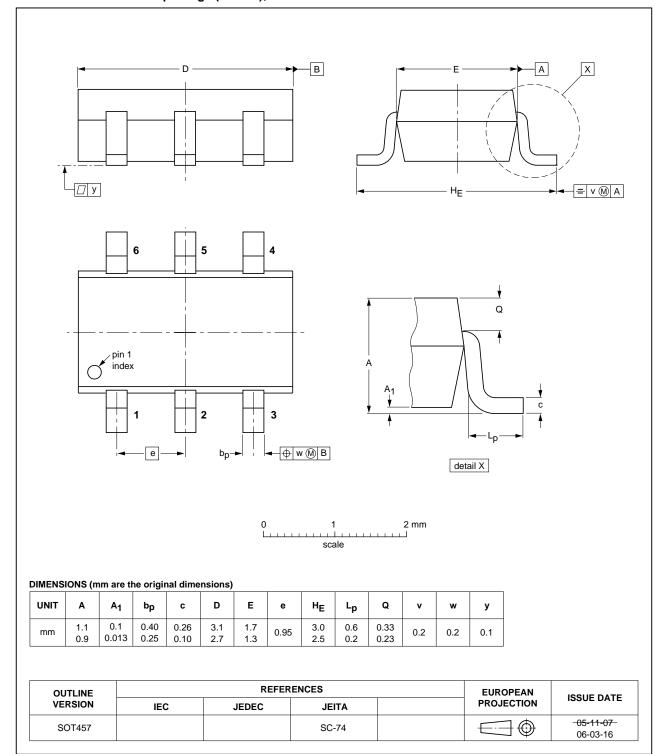
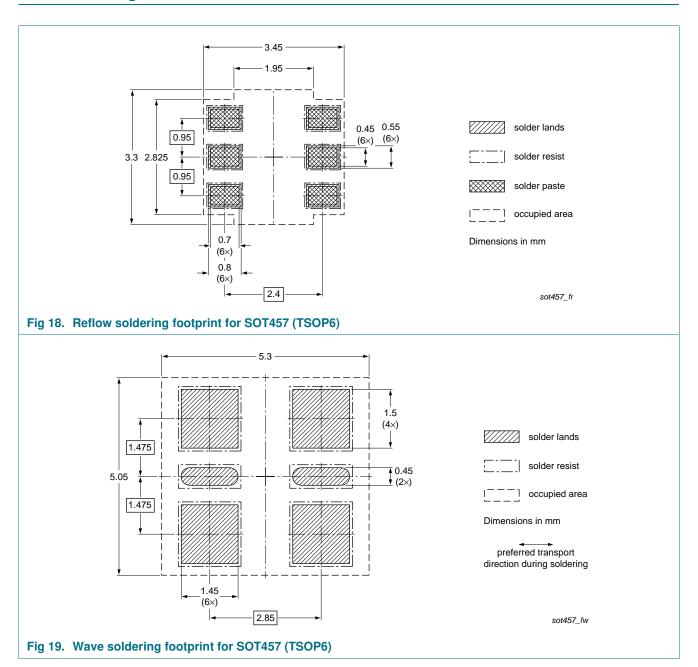


Fig 17. Package outline SOT457 (TSOP6)

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# 9. Soldering



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# 10. Revision history

# Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMN48XP v.1	20110421	Product data sheet	-	-

#### 20 V, 4.1 A P-channel Trench MOSFET

# 11. Legal information

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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